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BPW77NA, BPW77NB

Vishay Semiconductors



Silicon NPN Phototransistor, RoHS Compliant



FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): Ø 4.7
- · High photo sensitivity
- High radiant sensitivity
- · Suitable for visible and near infrared radiation
- · Fast response times
- Angle of half sensitivity: $\phi = \pm 10^{\circ}$
- · Base terminal connected
- Hermetically sealed package
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

· Detector in electronic control and drive circuits

DESCRIPTION

BPW77 is a silicon NPN phototransistor with high radiant sensitivity in hermetically sealed TO-18 package with base terminal and glass lens. It is sensitive to visible and near infrared radiation.

PRODUCT SUMMARY						
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)			
BPW77NA	7.5 to 15	± 10	450 to 1080			
BPW77NB	> 10	± 10	450 to 1080			

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

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ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
BPW77NA	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
BPW77NB	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
L					

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Collector base voltage		V _{CBO}	80	V		
Collector emitter voltage		V _{CEO}	70	V		
Emitter base voltage		V _{EBO}	5	V		
Collector current		Ι _C	50	mA		
Collector peak current	$t_p/T=0.5,t_p\leq 10\ ms$	I _{CM}	100	mA		
Total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	250	mW		
Junction temperature		Tj	125	°C		
Operating temperature range		T _{amb}	- 40 to + 125	°C		
Storage temperature range		T _{stg}	- 40 to + 125	°C		
Soldering temperature	t ≤ 5 s	T _{sd}	260	°C		
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	400	K/W		
Thermal resistance junction/gase		R _{thJC}	150	K/W		

Note

 $T_{amb} = 25$ °C, unless otherwise specified



COMPLIANT



Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

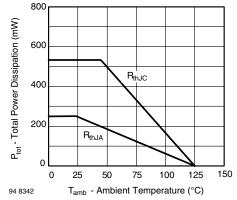


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V	
Collector emitter dark current	$V_{CE} = 20 V, E = 0$	I _{CEO}		1	100	nA	
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		6		pF	
Angle of half sensitivity		φ		± 10		deg	
Wavelength of peak sensitivity		λ _p		850		nm	
Range of spectral bandwidth		λ _{0.1}		450 to 1080		nm	
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ I_C = 1 \text{ mA}$	V _{CEsat}		0.15	0.3	V	
Turn-on time	V_{S} = 5 V, I_{C} = 5 mA, R_{L} = 100 Ω	t _{on}		6		μs	
Turn-off time	V_{S} = 5 V, I_{C} = 5 mA, R_{L} = 100 Ω	t _{off}		5		μs	
Cut-off frequency	V_{S} = 5 V, I_{C} = 5 mA, R_{L} = 100 Ω	f _c		110		kHz	

Note

 T_{amb} = 25 °C, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light ourrent	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$,	BPW77NA	I _{ca}	7.5 15	mA		
Collector light current	$V_{CE} = 5 V$	BPW77NB	I _{ca}	10			mA

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

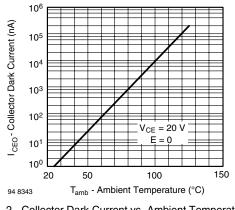


Fig. 2 - Collector Dark Current vs. Ambient Temperature

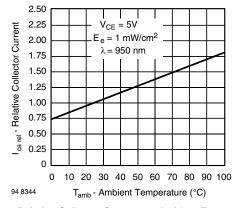


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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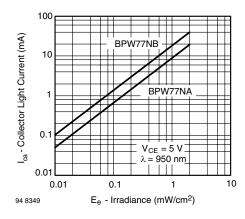


Fig. 4 - Collector Light Current vs. Irradiance

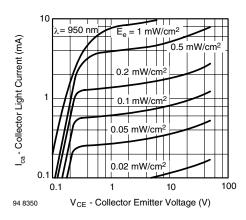


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

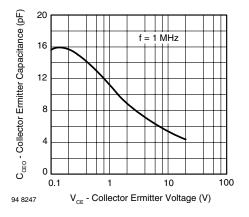


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

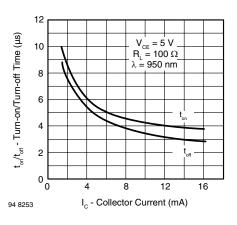


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

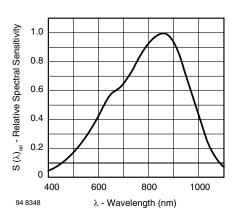


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

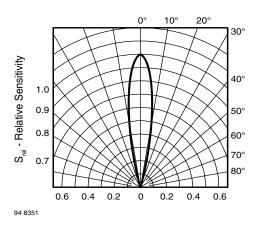


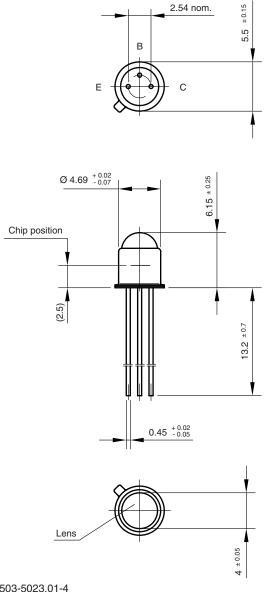
Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

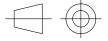


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PACKAGE DIMENSIONS in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.503-5023.01-4 Issue:1; 01.07.96 96 12180



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